

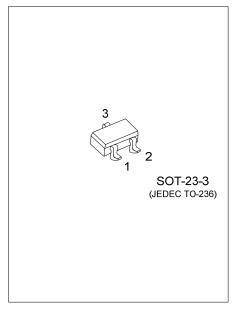
UNISONIC TECHNOLOGIES CO., LTD

UP2518 PNP TRANSISTOR

LOW V_{CE(SAT)} PNP SILICON POWER TRANSISTORS

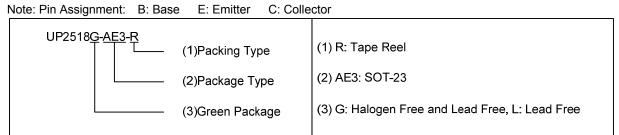
FEATURES

- * Extremely low collector-emitter saturation voltage $V_{\text{CE}(\text{SAT})}$ and corresponding extremely low equivalent on-resistance R_{CE(SAT)} $(97m\Omega \text{ at } 1.5A)$
- * High collector current capability(1.5A)
- * High peak pulse current up to 6A
- * High collector current gain

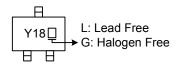


ORDERING INFORMATION

Ordering Number		Dooksays	Pin Assignment			Dealing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UP2518L-AE3-R	UP2518G-AE3-R	SOT-23	В	Е	С	Tape Reel	



MARKING



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■ **ABSOLUTE MAXIMUM RATING** (T_A= 25°C, unless otherwise stated)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-20	V
Collector-Emitter Voltage		V_{CEO}	-20	V
Emitter-Base Voltage		V_{EBO}	-5	V
Peak Pulse Current (Note 2)		I _{PEAK}	-6	Α
Continuous Collector Current		Ic	-1.5	Α
Base Current		I _B	-500	mA
Power Dissipation (Note 3)	T _A =25°C	P_{D}	625	mW
Junction Temperature		T_J	+150	°C
Storage Temperature		T _{STG}	-55 ~ + 150	°C

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 - 2. Pulse width=300µs. Duty cycle≤2%.
 - 3. Assume the device is mounted and measured on a ceramic substrate15x15x0.6mm.

■ **ELECTRICAL CHARACTERISTICS** (T_A= 25°C, unless otherwise stated)

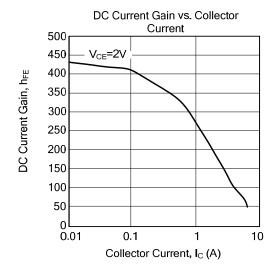
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_CBO	I _C = -100μA	-20	-65		V
Collector-Emitter Breakdown Voltage	BV_CEO	I _C = -10mA (Note)	-20	-55		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E = -100μA	-5	-8.8		V
Collector Cut-Off Current	I_{CBO}	V _{CB} = -15V			-100	nA
Emitter Cut-Off Current	I _{EBO}	V _{EB} = -4V			-100	nA
Collector Emitter Cut-Off Current	I _{CES}	V _{CES} = -15V			-100	nA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I_C = -100mA, I_B = -10mA (Note)		-16	-40	mV
		I _C = -1A, I _B = -20mA (Note)		-130	-200	mV
		I_C = -1.5A, I_B = -50mA (Note)		-145	-220	mV
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I_C = -1.5A, I_B = -50mA (Note)		-0.87	-1.0	V
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	V_{CE} = -2V, I_{C} = -2A (Note)		-0.81	-1.0	V
DC Current Gain	h _{FE}	V_{CE} = -2V, I_{C} = -10mA (Note)	300	475		
		V_{CE} = -2V, I_{C} = -100mA (Note)	300	450		
		V_{CE} = -2V, I_{C} = -2A, (Note)	150	230		
		V_{CE} = -2V, I_{C} = -4A, (Note)	35	70		
		V _{CE} = -2V, I _C = -6A, (Note)	15	30		
Transition Frequency	f_T	V_{CE} =-10V , I_{C} = -50mA, f=100MHz	150	180		MHZ
Output Capacitance	C_OB	V _{CB} = -10V, f=1MHz		21	30	pF
Turn-On Time	t _(ON)	V _{CC} = -10V, I _C = -1A		40		ns
Turn-Off Time	t _(OFF)	I _{B1} = I _{B2} = -20mA		670		ns

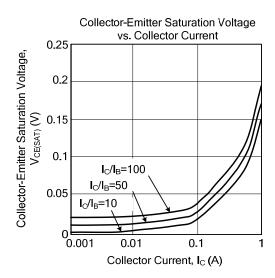
Note: Measured under pulsed conditions. Pulse width=300µs. Duty cycle≤2%.

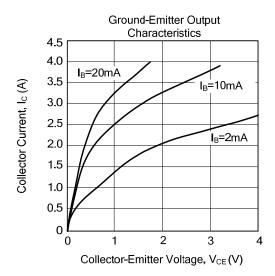


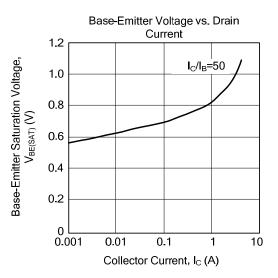
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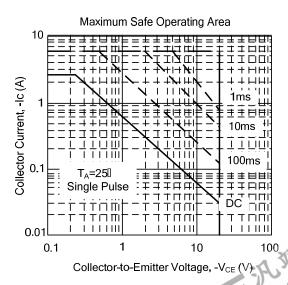
■ TYPICAL CHARACTERISTICS











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